
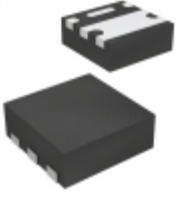

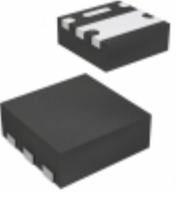


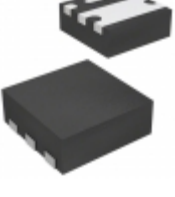


	<h2>SIA448DJ-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA448DJ-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 12A SC70-6L</p> <p>Datenblätter:  SIA448DJ-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 54000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA448DJ-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 20V 12A SC70-6L
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	54000 pcs Stock
detaillierte Beschreibung	N-Channel 20V 12A (Tc) 3.5W (Ta), 19.2W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.5W (Ta), 19.2W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Tc)
Rds On (Max) @ Id, Vgs	15 mOhm @ 12.4A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	35nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	1380pF @ 1V
Antriebsspannung (Max Rds On, Min Rds On)	1.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA448DJ-T1-GE3CT

SIA448DJ-T1-GE3 ist neu im Original, Suche SIA448DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA448DJ-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA448DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA446DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 150V 7.7A SC70-6L</p>	 <p>SIA447DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 12A SC-70-6L</p>	 <p>SIA450DJ-T1-E3 Vishay / Siliconix MOSFET N-CH 240V 1.52A SC70-6</p>	 <p>SIA447DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 12A SC-70-6L</p>
 <p>SIA447DJ-T1-E3 VISHAY VISHAY QFN-6</p>	 <p>SIA449DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 12A SC70-6</p>	 <p>SIA446DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 7.7A SC70-6L</p>	 <p>SIA449DJ-GE3 Vishay Precision Group SIA449DJ-GE3 VISHAY</p>

heiße Teile

Mehr

⊛ SIA427DJ-T1-GE3	↔ SIA427DJ-T1-GE3	⇒ SIA429DJ-T1-GE3	D SIA429DJ-T1-GE3	⇒ SIA430DJ-T1-GE3
↳ SIA430DJ-T1-GE3	⊛ SIA431DJ	D SIA431DJ-T1	⇒ SIA431DJ-T1-GE3	⇒ SIA431DJ-T1-GE3
⊛ SIA432DJ-T1-GE3	↳ SIA432DJ-T1-GE3	⊛ SIA433EDJ	↔ SIA433EDJ-T1-GE3	⇒ SIA433EDJ-T1-GE3
D SIA436DJ-T1-GE3	⊛ SIA436DJ-T1-GE3	↳ SIA443DJ-T1-GE3	⊛ SIA443DJ-T1-GE3	⇒ SIA444DJ-T1-GE3
⇒ SIA444DJ-T1-GE3	↔ SIA445EDJ-T1-GE3	⊛ SIA445EDJ-T1-GE3	↳ SIA447DJ-T1-GE3	⇒ SIA447DJ-T1-GE3
↔ SIA448DJ-T1-GE3	⇒ SIA449DJ-GE3	D SIA450DJ-T1-GE3	⊛ SIA450DJ-T1-GE3	↳ SIA4528-100K
⊛ SIA4528-330K	D SIA4528-470K	⇒ SIA453EDJ-T1-GE3	↔ SIA453EDJ-T1-GE3	⇒ SIA456DJ-T1-GE3
↳ SIA456DJ-T1-GE3	⊛ SIA483DJ-T1-GE3	↔ SIA483DJ-T1-GE3	⇒ SIA513DJ-T1-E3	⇒ SIA517DJ-T1-GE3
⊛ SIA517DJ-T1-GE3	↳ SIA517DJ-T4-GE3	⊛ SIA519EDJ-T1-GE3	D SIA519EDJ-T1-GE3	⇒ SIA533EDJ-T1-GE3
↔ SIA533EDJ-T1-GE3	⊛ SIA778DJ-T1-GE3	↳ SIA778DJ-T1-GE3	⊛ SIA811ADJ-T1-GE3	⇒ SIA811ADJ-T1-GE3

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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